

Interaction effects and the metallic phase in p-SiGe

P.T. Coleridge, A.S. Sachrajda and P. Zawadzki

Institute for Microstructural Sciences, National Research Council, Ottawa, Ontario, K1A 0R6, Canada
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Magnetoresistance results are presented for p-SiGe samples on the metallic side of the $B=0$ metal-insulator transition. The results cannot be understood within the framework of standard theories for quantum corrections of a weakly interacting 2-dimensional system. In particular no logarithmic dependence on temperature is observed, at low fields, in either the longitudinal or Hall resistivities despite evidence in the magnetoresistance of weak localisation effects. Further, the Hall coefficient shows a strong logarithmic dependence on field. The results are better explained by renormalisation group theories and by an anomalous Hall effect associated with strong spin-orbit coupling in the presence of a background spin texture.

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A. Introduction

Recent experiments indicating the existence of a metallic state and a metal-insulator transition (MIT) in two-dimensional (2-D) semiconductor systems continue to attract attention¹. There is, as yet, no general consensus about the origin of the metallic behaviour and it remains a controversial topic. The metallic behaviour appears in strongly interacting systems where r_s (the ratio of the interaction energy to the kinetic energy) is large, typically 5 to 20 and the Coulomb interaction energy is by far the largest energy in the problem. While the existence of a MIT in 2-dimensional systems contradicts the well established one parameter scaling theory for non-interacting systems², it is not *a priori* forbidden for strong interactions³ and the observation of good scaling behaviour⁴, with symmetry about the critical density, supports the view that this is a genuine transition, driven by the interactions. This is also consistent with predictions of renormalisation group (RG) theories⁵⁻⁸ that a low temperature metallic phase can exist when interactions and disorder are both present.

An alternative view⁹ is that there is no transition, just a cross-over from weakly localised to strongly localised behaviour, and that the strong interactions do not significantly modify the basic Fermi liquid character. Large

values of r_s are almost inevitably associated with low densities and Fermi energies ($k_B T_F$) that are not much larger than the measuring temperatures so effects associated with the small Fermi degeneracy are likely to be significant. It is argued that these can fully account for the metallic-like increase in resistivity with temperature and that weak localisation and interaction effect corrections are present but concealed by the larger semi-classical effects.

Experimental support for this second viewpoint has recently been presented based on results obtained in p-GaAs¹⁰ and p-SiGe¹¹. In both cases the $B=0$ resistivity shows no direct evidence of a $\ln T$ dependence, the standard signature of both weak localisation and interaction effects. The magnetoresistance, however, has the characteristic negative peak associated with the destruction, by dephasing, of a weak localisation correction. Also the Hall coefficient shows a $\ln T$ dependence, interpreted as evidence for interaction corrections. The magnitude of both these terms is consistent with the standard predictions and it is argued the behaviour is that of an entirely conventional Fermi liquid, despite the large values of r_s .

Similar measurements, in p-SiGe samples, are presented here¹². The experimental data is consistent with these results but more detailed and is interpreted in a rather different fashion. The Hall data, in particular, shows a rich variety of field and temperature dependences that cannot be explained by the standard theories. It is suggested these new phenomena are associated, at least in part, with the strong interactions and, while not explained completely, are more consistent with predictions of renormalisation group theories. This supports the view that the low temperature metallic behaviour is not that of a conventional Fermi liquid but should be directly associated with the strong interactions.

B. Theory: weak interactions

Because the data presented below is discussed, initially, in terms of the quantum corrections for weakly interacting systems it is convenient to summarise the standard theoretical treatments of this¹³⁻¹⁵. The theories start with a semi-classical description of the transport, where the diffusion of electrons at the Fermi level is considered to obey classical dynamics and introduce quantum effects as small corrections. Drude-Boltzmann theory gives the zero field conductivity as

$$\sigma_0 = n_s e^2 \tau / m^* = \frac{g_s}{2} k_f l \frac{e^2}{h} \quad (1)$$

where n_s is the carrier density, τ the transport lifetime, m^* the effective mass, g_s the spin degeneracy, k_f the Fermi wavevector and l the mean free path. In a magnetic field the conductivity components are given by

$$\sigma_{xx}(B) = \frac{\sigma_0}{(1 + \mu^2 B^2)}; \quad \sigma_{xy}(B) = \mu B \sigma_{xx}(B) \quad (2)$$

where the mobility $\mu = e\tau/m^*$. Quantum interference introduces a weak localisation correction to this conductivity with a logarithmic temperature dependence

$$\Delta\sigma_{xx}^{wl}(T) = \alpha p (e^2/\pi h) \ln(k_B T \tau / \hbar) \quad (3)$$

where it is assumed the phase breaking time τ_ϕ varies as T^{-p} . The amplitude α is expected to be 1 for normal scattering (-0.5 for pure spin-orbit scattering and 0 for spin scattering) but may also be reduced by other factors such as anisotropic scattering.

A similar $\ln T$ dependence results from the Coulomb interaction effect

$$\Delta\sigma_{xx}^{ee}(T) = (1 - \frac{3F^*}{4})(e^2/\pi h) \ln(k_B T \tau / \hbar). \quad (4)$$

Two processes, with opposite signs, contribute here. An exchange term (singlet channel), involving only small momentum transfers, and a Hartree term (triplet channel) involving F^* , the Fermi surface average of the screened Coulomb interaction. Increasing F^* implies a smaller total correction and an increased tendency towards delocalising behaviour. For Thomas-Fermi screening $F^* < 1$ but it may, in principle, be larger. In this case a weakly interacting theory is inappropriate and should be replaced by more sophisticated approaches but with trends that are probably still given correctly by eqn.4. Large values of F^* lead to negative coefficients for the interaction term which may even overcome the weak localisation term and result in a total negative, or delocalising, coefficient. Values of F^* larger than one are frequently obtained from fits to experimental data^{16,17}.

Application of a magnetic field allows the weak localisation and interaction terms to be separated. At low fields dephasing of the weak localisation term gives a characteristic, negative magnetoresistance,

$$\Delta\sigma_1(B) = \alpha \frac{e^2}{\pi h} [\Psi(\frac{1}{2} + \frac{\tau_B}{2\tau_\phi}) - \Psi(\frac{1}{2} + \frac{\tau_B}{2\tau}) + \ln(\frac{\tau_\phi}{\tau})] \quad (5)$$

where Ψ is the digamma function and $\tau_B = \hbar/2eDB$ with D (the diffusion constant) $= v_F^2/2\tau$. In terms of the variable $h = 2\tau_\phi/\tau_B$ (proportional to B and not to be confused with the Planck constant) this function varies as $h^2/24$ for small h and as $\ln(h)$ for $1 \ll h \ll \tau_\phi/\tau$. Fitting to the characteristic shape, particularly at small B , allows an experimental determination of α and τ_ϕ .

The interaction term is unaffected by small magnetic fields but at higher fields the singlet part is modified by

Zeeman spin-splitting. This leads to a positive magnetoresistance given by

$$\Delta\sigma_2(B) = -(e^2/\pi h)(F^*/2)G(b) \quad (6)$$

where $b = g\mu_B B/k_B T$ with g the g-factor of the spins. The function $G(b)$ is known: for small b $G(b) = 0.084b^2$ and for large b it varies as $\ln(b/1.3)$ and can be calculated in the intervening region¹⁷.

In addition to these terms there is also the classical magnetoconductance, eqn.2, which gives a correction with a quadratic dependence

$$\Delta\sigma_{xx}(B) \approx -\sigma_0 \mu^2 B^2. \quad (7)$$

Interactions do not affect the Hall conductivity, σ_{xy} , but the weak localisation corrections appear a factor of two larger. When the Hall coefficient ($R_H = \rho_{xy}/B$) is obtained by inverting the conductivity tensor the weak localisation terms therefore cancel and

$$\Delta R_H/R_H = -2\Delta\sigma_{xx}^{ee}/\sigma_{xx}. \quad (8)$$

A logarithmic temperature dependence in the Hall coefficient is therefore expected with an amplitude proportional to the strength of the electron-electron interactions but independent of weak localisation.

At low fields, when ρ_{xx} is obtained by inverting the conductivities, the $\ln(T)$ weak localisation and interaction effect correction terms appear additively in the same way as in σ_{xx} but the quadratic classical term is automatically cancelled. At larger fields, when μB becomes significant, the admixture of σ_{xx} and σ_{xy} contributions introduces an additional $\ln(T)$ term¹⁸, proportional to $(\mu B)^2$. For B sufficiently large for this to be important the weak localisation is usually suppressed and this quadratic term is positive with an amplitude proportional to $(1 - \frac{3}{4}F^*)$.

C. Samples

The samples used in this investigation are from a set of p-type modulation doped strained Si-Ge quantum wells which exhibit MIT behaviour¹⁹. They were grown using a low temperature UHV-CVD process and have a Si buffer layer, a 40nm Si_{0.88}Ge_{0.12} quantum well, a spacer layer (of variable thickness), a boron doped layer and a thin Si cap. The holes reside in an approximately triangular SiGe quantum well, produced by the asymmetric doping, which is strained because it is lattice matched to the Si substrate. It has been established that they are in almost pure $|M_J| = 3/2$ states, well decoupled from other hole states by strain and confinement²⁰. The two samples used were Sample A with a density of $5.7 \times 10^{11} \text{cm}^{-2}$ which is deep in the metallic phase and sample B, with a density of $1.2 \times 10^{11} \text{cm}^{-2}$, close to the critical density for the MIT, which is at approximately $1.0 \times 10^{11} \text{cm}^{-2}$.

Values of r_s are approximately 4 and 6, respectively, for the two samples.

Effective mass values are known only approximately in this system. Measurements from the temperature dependence of the Shubnikov-de Haas oscillations gave values of $0.305m_0$ for sample A²¹ and approximately $0.23m_0$ for sample B. These are significantly larger than the band mass of $0.20m_0$ ²² and may reflect a breakdown of the standard Lifshitz-Kosevitch expression in a system where strong quantum corrections are expected. It should be noted that high field cyclotron resonance measurements^{23,24} have given values as low as $0.18m_0$.

The g-factor in p-SiGe is not well known but is of order 4 in perpendicular fields²⁵. In sample A the low field Shubnikov-de Haas (SdH) oscillations appear initially at odd filling factors²¹, corresponding to a Zeeman splitting of the Landau levels sufficiently large that $gm^*/m_0 > 1$. With $m^*/m_0 \approx 0.25$ this means g is probably slightly larger than 4. In sample B the SdH oscillations appear initially at even filling factors so $gm^*/m_0 < 1$. Using $m^* = 0.23m_0$ and taking gm^*/m_0 to be 0.8 ± 0.2 gives $g = 3.6 \pm 1$. In tilted fields, the almost pure $|M_J| = 3/2$ character of the heavy hole states means the g-factor varies accurately as $B\cos\theta$ ²¹, where θ is the tilt angle away from the perpendicular. Therefore, unlike the situation in Si-MOSFETs and n-GaAs heterojunctions, tilting the magnetic field leaves the relative contributions from orbital and spin splitting terms unchanged but a function of $B\cos\theta$.

D. Experimental procedures

Measurements were made using a DC bridge²⁶, with current reversal at 15Hz. Two cryostats were used, a dilution refrigerator giving temperatures below 100mK and a sorption pumped He3 system that could achieve sample temperatures down to 270mK. In both cases thermometry was in a field free region, with the sample cooled essentially by the copper leads. Measurements using a calibrated, field insensitive, thermometer in place of the sample indicated the temperature gradients were less than 5mK.

Resistance measurements, especially in sample B, showed an unusual sensitivity to measuring current at the lowest temperatures. Currents as low as 1nA, corresponding to voltages of only a few microvolts, produced detectable metallic-like non-linearities in the I-V characteristics and made accurate low temperature measurements of the zero field resistivity difficult. This is attributed, at least to some extent, to the proximity of the MIT. Measurements in magnetic fields, especially near $B=0$, were complicated by an extreme sensitivity to sweep rate and long thermal time constants. This is not completely understood although it is accounted for, in part, by heating associated with flux jumps as field in the superconducting magnet was reversed. Care

was taken to average results from up and down sweeps and to check frequently (making corrections if necessary) that the measured resistances were the same in static and swept fields.

E. Experimental results

Magnetoresistance data from sample A is shown in figure 1. At zero field the monotonic metallic-like increase of resistance with temperature, characteristic of samples showing a MIT, can be clearly seen. Over the temperature range shown (0.15 - 2.2K) a logarithmic weak localisation term (eqn.3) would give a *decrease* of resistance with increasing temperature of order 50-100 ohms/square, roughly a factor of two larger and in the opposite sense to the observed variation. The well defined low field negative magnetoresistance, with a width that increases with temperature, is attributed to weak localisation and the positive magnetoresistance at higher fields to a Zeeman interaction term.

Attempts to fit the field dependence to a combination of eqns. 5 and 6 failed, even when the full field dependence of $G(b)$ was used, with the g-factor as a separate fitting parameter for a total of five. The alternative approach taken was therefore to fit the data to eqn. 5 at the lowest fields, using just three parameters: τ (determined essentially by the $B=0$ value of the resistivity), τ_ϕ and an amplitude α . The results of these fits are shown in figure 1. Care was taken to establish that the parameters were insensitive to the precise range of B and also that they were not significantly altered when this range was extended and an extra quadratic term added. The values of τ_ϕ , shown in figure 2, are similar to those obtained from other measurements in p-SiGe²⁷⁻²⁹. Values of α were 0.7 at low temperatures decreasing to 0.6 at higher T.

The residues from these fits are shown in fig.3a. Plotted against B/T (fig. 3b) they collapse onto a single curve which gives some confidence that the fitting procedure has successfully separated the weak localisation term from a Zeeman interaction term which is a function of B/T . This curve is not, however, given by eqn.6. The solid line in fig. 3b is $G(b)$, fitted to the curve for larger values of B/T , with $F^* = 2.45$ and a g-factor of 6.4. It deviates significantly from the data at low values of B/T and the value for g is somewhat larger than expected.

The most important conclusion from this fitting procedure, despite only qualitative agreement between theory and experiment, is the large value of F^* . This implies that the interactions are strong and that the standard theory, where it is implicitly assumed that $F^* \leq 1$, is inadequate. Expressions for the Zeeman interaction term using renormalisation group theory have been derived, for $b \gg 1$, by Finkel'stein⁶

$$\Delta\sigma_2(B) = -(e^2/\pi h) 2 \left[\frac{1+\gamma_2}{\gamma_2} \ln(1+\gamma_2) - 1 \right] \ln(b) \quad (9)$$

and for $b \ll 1$ by Castellani *et al*^{7,8}

$$\Delta\sigma_2(B) = -0.084(e^2/\pi h)\gamma_2(1 + \gamma_2)b^2. \quad (10)$$

Here the coupling constant γ_2 is a measure of the renormalised interaction strength for the triplet scattering channel. It reduces to $F^*/2$ in the limit of weak interactions.

The dashed lines in fig. 3b show fits using these two equations in the high field and low field limits respectively, using $g = 3.6$ and $\gamma_2 = 2.6$ in both cases. Making a reasonable interpolation between the high field and low field expressions this gives a much better description of the experimental data. The value of g is perhaps a little small but is predominantly determined by the low field quadratic regime where experimental errors are relatively large.

For sample B the magnetoresistance data (figure 4) is shown as the conductivity obtained by inverting measured values of ρ_{xx} and ρ_{xy} . Again the increase in conductivity with decreasing temperature is in the opposite sense to that expected for a weak localisation lnT term which, over the temperature range shown, should be of order $0.5 e^2/h$. Because the ratio τ_ϕ/τ is significantly smaller than in sample A, the weak localisation peak is only poorly defined and the behaviour is dominated by a quadratic dependence on field which is a combination of the classical term (eqn. 7) and the low field Zeeman interaction term (eqns.6 or 10). Because the g -factor varies quite precisely as $\cos\theta$ these results, when plotted against $B\cos\theta$, are essentially independent of tilt. Spurious sweep rate effects associated with heating (noted above) are dependent on the total field and are less apparent in tilted fields so it was convenient to use tilted field data (at an angle of 69°) for a detailed analysis of the field and temperature dependences.

The structure at low fields is sufficiently weak that the fitting procedure developed for sample A could not be used: the equations became ill-conditioned and gave imprecise and interdependent values of α and τ_ϕ . The fit is relatively insensitive to the exact value of α (see also Senz *et al*²⁹) so this was fixed (at 0.65) and just three adjustable parameters used: τ , τ_ϕ and a quadratic coefficient. As can be seen in figure 4 these gave very good descriptions of the data provided the fits were restricted to the field region where the Zeeman interaction term is expected to be quadratic in B . Values of τ_ϕ are shown in figure 2.

When the weak localisation and classical mobility terms are subtracted off, the residues should be the Zeeman interaction term. This is plotted against B/T in figure 5. The collapse onto a single curve is not as good as in sample A, mainly because the classical mobility correction is relatively large (especially at higher temperatures) and there is some uncertainty about how σ_0 should be defined³⁰. Using a g -factor of 3.6 the quadratic fit shown gives $\gamma_2 = 0.7 \pm 0.2$ if eqn. 10 is used or $F^* = 2.5$ using eqn.6. In this case the deviation away from

quadratic behaviour at higher fields is better described by eqn. 6 with $F^* = 2.5$ than by the RG eqn.9 with $\gamma_2 = 0.7$.

In both samples the amplitude of the Zeeman interaction term gives large values of F^* (or of γ_2) consistent with strong Coulomb interactions. Another measure of F^* , at least according to the standard theory, is obtained by looking at the magnitude of the lnT term in the Hall coefficient (eqns.4 and 8). In practice, as shown in figure 6 where R_H is plotted against field, the situation is more complicated. In both samples R_H is strongly field dependent and at low fields, where the lnT term is expected, there is no detectable temperature dependence. The absence of a low field lnT term (see also the inset to figure 6b³¹) in R_H parallels the absence of a lnT dependence in the $B=0$ conductivity data. For the conductivity alone this might perhaps reflect a fortuitous cancellation between weak localisation and interaction terms of the opposite sign but the absence of any T dependence in the Hall coefficient, which is affected only by interaction corrections, shows that the lnT weak localisation and interaction terms must separately vanish despite the evidence from the magnetoresistance of weak localisation. There is no explanation for this within the framework of the “standard” theory for quantum corrections. Similarly there is no explanation for the strong field dependence of R_H near $B=0$.

At higher fields this field dependence persists and temperature dependence also eventually appears. A semi-log plot of the data, figure 7, shows that once developed this is, indeed, linear in lnT. For sample A the slope, $\Delta R_H/(R_H \ln T)$, is -0.024, independent of field. For sample B it varies with field with a maximum value (at 0.5 tesla) of -0.085. Expressed in terms of an equivalent amplitude for $\Delta\sigma_{xx}^{ee}$ (eqns.4 and 8) these correspond respectively to $F^* = 0.6$ and 0.74. The lnT term at higher fields is therefore consistent with other measurements in p-SiGe^{27,29} where values of F^* , determined in the same way, were found to be about 0.85. In these measurements no special attention was paid to the very low field region and non-linearities in R_H were not reported.

The lnT term develops in a different way in the two samples. In sample A there is a fairly abrupt transition from a high T regime, where R_H is temperature independent, to a low T limit where the slope appears to be independent of B. The breakpoint where this change of slope occurs is found empirically to depend linearly on B with $(B/T)_{\text{break}} \approx 0.9$ tesla/kelvin. In sample B it develops at lower fields and, as shown in the inset to figure 7, the slope increases linearly with field with a low field extrapolation corresponding to a vanishing slope at $B=0$. In sample B measurements of R_H at higher fields are complicated by the onset of the quantum oscillations which, because of their long period, cannot be separated from the background variation.

As previously noted the B-dependence of R_H is not understood. Semi-log plots of the data (figure 8) show that at low fields R_H increases approximately as lnB and at

higher fields, when the temperature dependence appears, the increase remains predominantly logarithmic but with a (T dependent) reduction in the slope. The low field slopes, given by $\Delta R_H/(R_H \ln B)$, are 0.11 and 0.18 for samples A and B respectively. If attributed to a coulomb interaction term they correspond to conductivity corrections (using eqn.8) of $\Delta\sigma_{xx}^{ee} = -2.4(e^2/\pi h) \ln(B)$ and $-0.8(e^2/\pi h) \ln(B)$. These are relatively large effects, particularly for sample A, and should be readily observed in the direct measurements of σ_{xx} (or ρ_{xx}). It should be noted that expressed in terms of a conductivity correction, the amplitude of the B dependence in R_H is larger for the higher density sample, deeper into the metallic phase. Indeed, for both the samples it is, probably fortuitously, equal to the value of γ_2 derived by fitting the Zeeman interaction term.

F. Discussion

The data presented above cannot be understood within the framework of the standard theory for weakly interacting systems outlined above. One problem is a magnetoresistance consistent with weak localisation effects but without any sign of the corresponding $\ln T$ dependence in ρ_{xx} . A second problem is the large values of F^* extracted by fitting the Zeeman Interaction term without, again, any corresponding zero field $\ln T$ dependence. Thirdly, there is the strong $\ln B$ dependence of R_H , particularly near $B=0$.

The weak localisation peak in the low field magnetoresistance appears conventional. It can be fitted by the standard expression with values of τ_ϕ of the expected order of magnitude. If the dephasing occurs by inelastic carrier-carrier scattering in the limit of small momentum transfer values (sometimes known as Nyquist dephasing) τ_ϕ should be given by^{13,32,33}

$$\tau_\phi = \hbar f(g)/k_B T \quad (11)$$

where $f(g)$, with the conductance g in units of e^2/h , is $g/\ln(g/2)$ for $g \gg 1$ but of order g as g approaches 1. Figure 2 shows these values plotted with $f(g) = 7.4$ for sample A (where $g=15$) and 2.6 for sample B (where $g=2.6$). The experimental values of τ_ϕ are approximately 5 times smaller than this; similar discrepancies are also seen in Si-MOSFETs³² and in p-GaAs¹⁰. It is not clear whether this discrepancy is significant.

Interpreted according to the standard theory the Zeeman interaction term is very large, with values of F^* significantly larger than one. Similar discrepancies exist in Si-MOSFETs^{16,17}. Also the functional dependence on B/T appears to be incorrect. A plausible extension of the weakly interacting theory, with large values of F^* , might be able to explain the absence of a $\ln T$ term in σ_{xx} as a cancellation between a positive coefficient for the weak localisation correction and negative values of the interaction coefficient so $(\alpha p + 1 - \frac{3}{4}F^*)$ vanishes.

But R_H should then also have a $\ln T$ term, dependent only on the interactions, with a coefficient $(1 - \frac{3}{4}F^*)$. With αp (obtained from the magnetoresistance) of order 0.6 these coefficients cannot vanish simultaneously. Therefore, even if empirically adjusted to allow for large values of F^* , the standard theory cannot account for the absence of a $\ln(T)$ term in both σ_{xx} and R_H .

At low fields, according to the standard theories, interactions do not give a $\ln B$ dependence in the Hall coefficient and while the weak localisation function (eqn. 5) has a $\ln B$ dependence it is of the opposite sign and appears only for $1 \ll 2\tau_\phi/\tau_B \ll \tau_\phi/\tau$. In sample A, for example, this corresponds to fields less than .05 tesla and is a factor 3 or 4 times smaller than the term corresponding to the observed R_H dependence. The absence of a $\ln(B)$ term in σ_{xx} matching that in R_H cannot therefore be attributed to a fortuitous cancellation with a weak localisation term.

At high fields the Zeeman Interaction term has a $\ln(B)$ dependence. For, sample A, this corresponds to that measured in R_H to accuracy of about 20%. For sample B, where the $\ln(B)$ dependence in σ_{xx} could not be explicitly determined, the R_H value is also qualitatively consistent with eqn.9 and a fitted value of $\gamma_2 = 0.7$. In both cases, at higher fields, the *field* dependence of R_H can therefore probably be accounted for by the Zeeman interaction term but not the *temperature* dependence. The B/T dependence seen in the σ_{xx} data is not reproduced in the R_H data.

Some of these results can be understood within the framework of renormalisation group (RG) theories⁶⁻⁸. These involve a coupling constant γ_2 , related to the strength of spin density fluctuations. For weak interactions γ_2 reduces to $F^*/2$ but for strong interactions it may be dramatically enhanced by correlations. Disorder leads to a renormalisation of the interaction amplitudes and for weak disorder γ_2 is expected to increase with decreasing temperature. The localising $\ln T$ dependence is then replaced by scaling towards metallic behaviour with, in the $T=0$ limit, an eventual saturation at a finite resistivity. For strong disorder scaling is towards an insulating state so there should be a cross over from metallic to insulating behaviour as the disorder increases. In terms of the dimensionless resistivity r (in units of $\pi h/e^2$) the equations diverge when $r\gamma_2 \sim 1$ and the theory is unable to answer the question of whether a quantum critical point is expected at the cross-over.

RG theories account for the saturation of the low temperature resistivity at a finite value and the absence of a $\ln T$ term at $B=0$ (although they do not predict the exponential dependence on T that is frequently observed). The large values of F^* (or equivalently γ_2) needed to describe the magnitude of the Zeeman Interaction term are expected, also the observation that γ_2 seems to be larger in the higher density sample, further away from the critical density. The experimentally observed functional dependence of the Zeeman term also seems to be in better agreement with RG expressions than with $G(b)$.

One problem is that renormalisation implies γ_2 should increase with decreasing temperature in which case the functional dependence on B/T seen in figure 3b should be destroyed. This can probably be explained by the fact that most of the data is restricted to the low temperature region when the resistivity is close to saturation and γ_2 is no longer temperature dependent.

A further prediction of RG theory⁷ is that in the high field limit $\Delta\sigma_{xx}(T) = \beta(e^2/\pi h)\ln(T)$ where β has the universal value, $2\cdot 2\ln 2$ ($= 0.61$). High field in this case corresponds to a Zeeman splitting $g\mu_B B \gg k_B T$, ie $b \gg 1$. This universal dependence is not seen directly in σ_{xx} (it would correspond for example to a value of $\gamma_2 \approx 0.7$ in eqn. 9 for the Zeeman Interaction term) but a universal value of $\beta = 0.6$ does seem describe the temperature dependence of the high field, low temperature data for R_H in sample A. The cross-over to this behaviour, at $B/T \approx 0.9$ tesla/kelvin, corresponds to $b \approx 2$. That sample B does not behave in the same way may be associated with the fact that in this sample, close to the MIT, $r\gamma_2$ is of order 0.8 and in the regime when the RG equations are starting to fail.

The behaviour that cannot be understood, according to either the weakly interacting or RG theories, is the low field $\ln B$ dependence of R_H and the absence of a corresponding term in σ_{xx} . It would therefore appear that this is not a conventional interaction term but involves some other mechanism. Against this the correlation between the magnitude of the $\ln B$ dependence and density and the smooth transition to a high field behaviour which can be at least partly understood in terms of RG theory, suggests it is nevertheless related, in some way, to the strong interactions.

One clue is the absence of such behaviour in Si-MOSFETs where it might also be expected. Recent experiments in tilted fields³⁴, in good agreement with results in the literature for perpendicular fields, find R_H increases by less than 6% for in-plane fields up to 12T (perpendicular fields up to 0.5T). An essential difference between the two systems is the strong spin-orbit coupling in p-SiGe. This points to the field dependence of R_H as being a manifestation of the Anomalous Hall effect³⁵.

The Anomalous (or Extraordinary) Hall effect is best known in metallic ferromagnets where the Hall coefficient has a strong field dependence given by

$$\rho_{xy} = R_H B + R_s \mu_0 M \quad (12)$$

with M the magnetisation and where R_s is often significantly larger than R_H . This is not well understood theoretically. According to conventional understanding, it can be explained in ferromagnets in terms of interference between spin-orbit coupling and spin-flip scattering^{36,37}. An important feature of the theories is the requirement that the spin-up and spin-down populations are different and proportional to the magnetisation. The effect is also observed in magnetic semiconductors³⁸ and in materials having a ‘‘colossal magnetoresistance’’³⁹. A recent

theory⁴⁰ explains the results in this last example in terms of the effect of spin-orbit coupling on the ‘‘Berry phase’’ associated with a spin texture. It seems unlikely that a single theory can explain all occurrences of the anomalous Hall effect but a feature of all theoretical descriptions is the importance of the spin-orbit interaction and a magnetisation associated with some form of spin polarisation.

In Si-MOSFETs experiments in tilted fields⁴¹ show clearly that the spins are intimately connected with the MIT. For example, polarising the spins drives the system from a metallic state towards the insulating phase and there is evidence for a quantum phase transition into a ferromagnetically polarised ground state at the critical density⁴². In p-SiGe similar experiments^{43,44} show effects in the same sense but requiring fields at least an order of magnitude larger. This is to be expected, because the spins cannot be decoupled from the orbital motion and fields in the quantum limit, ie with a Landau level filling factors of order one, are required to produce a spin polarisation⁴⁵. There seems to be no fundamental reason to suppose that the spins do not play the same kind of role in p-SiGe as in MOSFETs, just that the strong spin-orbit coupling makes it difficult to probe this state by using tilted fields. The spin polarisation is, however, revealed indirectly through the anomalous Hall effect. It would be interesting to see if p-GaAs, where the spin-orbit coupling is also strong, shows similar effects.

Senz *et al*¹¹ have suggested that a conventional $\ln T$ weak localisation term is in fact present in p-SiGe and that the measured resistivity is the sum of this and a linear term associated with the temperature dependence of the dielectric screening function. These combine to give an *apparent* low temperature saturation of resistivity. In a similar analysis for the data reported here figure 8 shows both the measured conductivity and the conductivity with a putative weak-localisation correction, $\alpha p(e^2/\pi h)\ln(k_B T \tau/\hbar)$ subtracted off. The expected variation associated with temperature dependent screening, is given by the calculation of Gold and Dolgoplov⁴⁶ as

$$\sigma(T) = \sigma(0)[1 - C_p \frac{T}{T_F} + O(\frac{T}{T_F})^{3/2}]. \quad (13)$$

Similar results have also been obtained numerically by Das Sankar⁴⁷.

While the corrected data appears to have a predominantly linear dependence there is, in both samples, indications of an upturn, larger than the experimental errors, at low T . This upturn, which reflects directly the $\ln T$ dependence of the correction term added to either the saturation or approximately linear variation in the measured data, tends therefore to contradict the conclusions of Senz *et al*. Lower temperature data is, however, needed to decide this. The coefficients C_p are larger than expected. With the impurity scattering and interface roughness scattering dominating C_p for sample A is expected⁴⁸ to be 1.2 - 1.5, compared with an experimen-

tal value of 2.5 and in sample B the measured value of 5.9 is three times the expected value of about 2.

Hamilton *et al*⁴⁹ draw attention to similarities in the T dependence of p-GaAs and Si-MOSFETs. For large values of T/T_F , up to about 0.4, they find an approximately universal behaviour of $\Delta\sigma/\sigma$, consistent for example with temperature dependent screening. There is, however, little data for the range $T < .02T_F$ where any $\ln(T)$ dependence of interaction and weak localisation effects will be readily separable from semi-classical behaviour. Therefore, although it seems clear that temperature dependent screening (or similar semi-classical effects) are important at higher temperatures it seems unlikely that they can account for the absence of any observable $\ln T$ weak localisation term at zero field.

G. Conclusions

Transport data is presented for two p-SiGe samples on the metallic side of the MIT. The metallic behaviour and the large Zeeman interaction term cannot be understood within the theory of conventional weakly interaction quantum corrections but are more consistent with predictions of Renormalisation Group theories. Fitting to RG expressions gives values for the parameter γ_2 that are large and increase with increasing density.

The low field magnetoresistance shows evidence of the destruction, by dephasing, of a weak localisation term but there is no clear evidence of the corresponding $\ln T$ dependence, localising or delocalising, in either the conductivity σ_{xx} or in the Hall coefficient. Phase breaking times extracted from fits to the magnetoresistance are somewhat smaller than expected but of the expected order of magnitude. At higher fields, when the Zeeman splitting is larger than the temperature, a $\ln T$ dependence develops with some evidence, in the Hall coefficient, for the “universal” behaviour predicted, in this limit, by RG theory.

A strong and unexplained $\ln B$ dependence in the Hall coefficient is not reflected in the low field conductivity. This is tentatively associated with an anomalous Hall coefficient resulting from the large spin-orbit coupling in this system. If this interpretation is correct it demonstrates directly the development a spin polarisation similar to that reported for Si-MOSFETs and closely related to the strong spin density fluctuations predicted by RG theories.

This accumulated evidence supports the view that the metallic behaviour and MIT in p-SiGe cannot be adequately described by the standard theory for weak coulomb interactions but rather should be directly associated with the strong interactions.

H. Acknowledgements

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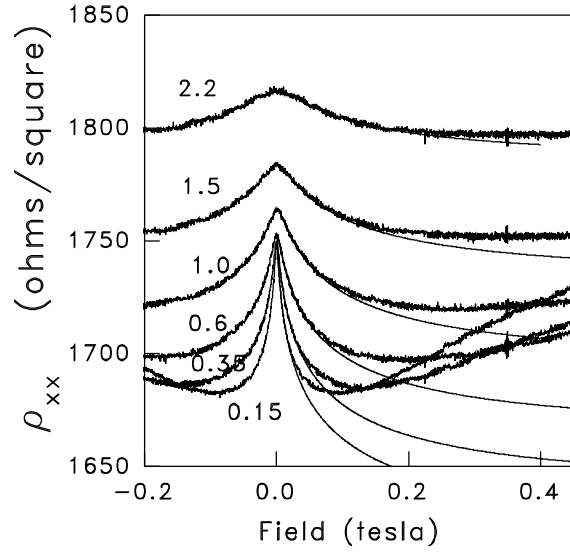


FIG. 1. Magnetoresistance data for sample A at temperatures of 0.15, 0.35, 0.6, 1.0, 1.5 and 2.2 K (top curve). Lines are fitted to the weak localisation peak (eqn.5) in the low field regime as described in the text.

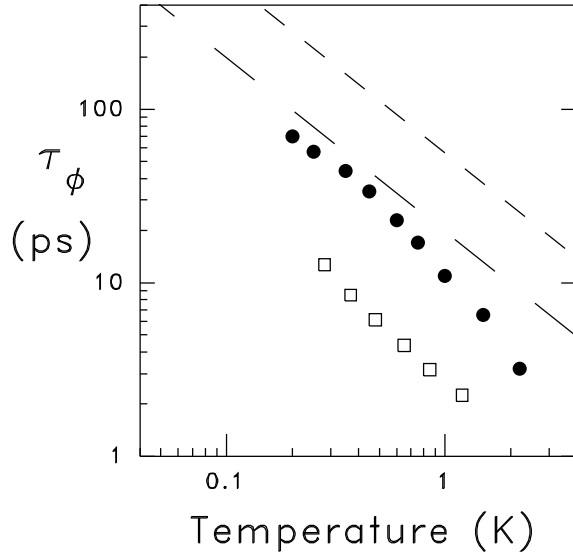


FIG. 2. Dephasing times, τ_ϕ , extracted from fits to the weak localisation peak in sample A (solid points) and sample B (open points). The lines are the values given by eqn.11 with $f(g) = 7.4$ (sample A, short dashes) and 2.6 (sample B, long dashes). For comparison τ , the transport lifetime is approximately 0.9ps in both samples.

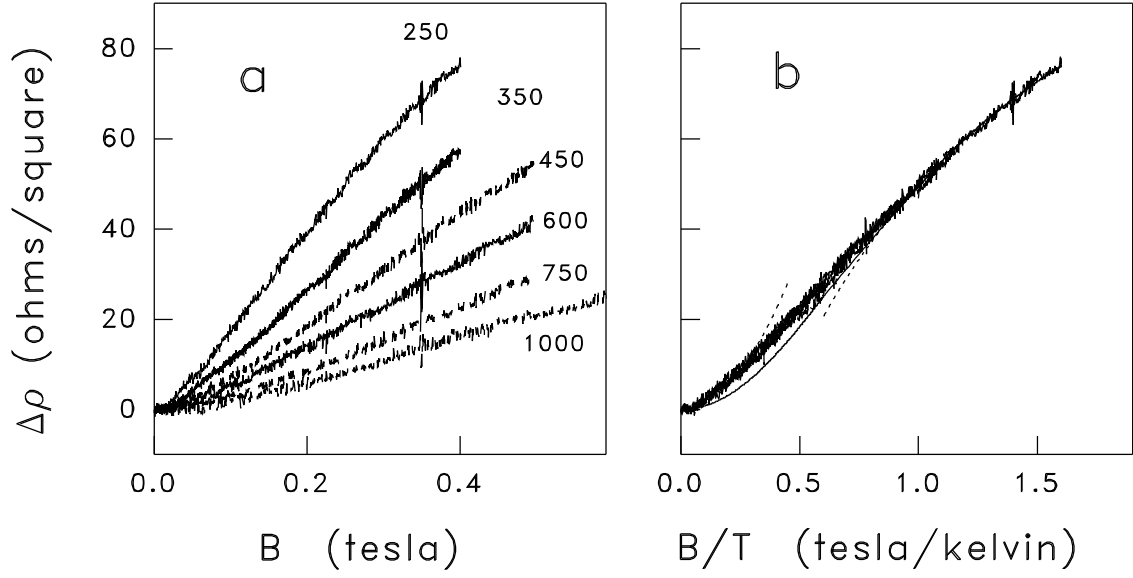


FIG. 3. (a) Residues from the weak localisation fits to the low field magnetoresistance for sample A. Temperatures are respectively 250 (largest resistivity values), 350, 450, 600, 750 and 1000 mK. (b) Data plotted against B/T . Solid line is a fit to $G(b)$ (eqn.6) and the dashed lines fits to eqns. 9 and 10. For $b=1$, B/T is approximately 0.4 tesla/kelvin.

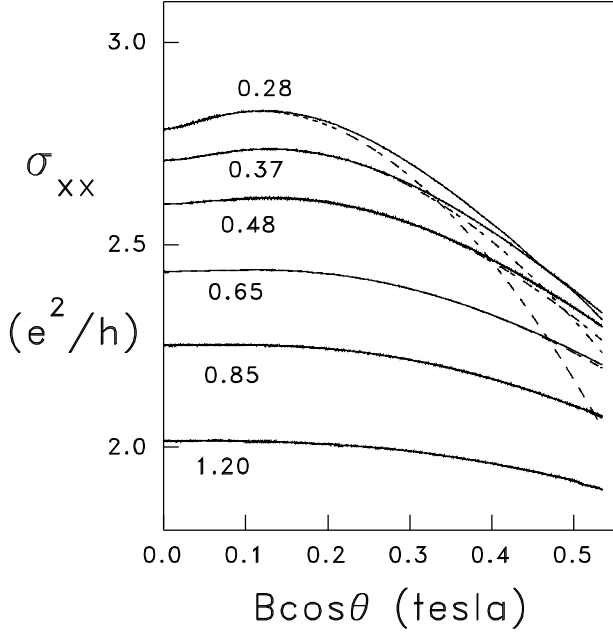


FIG. 4. Magnetic field dependence of the conductivity in sample B at temperatures of 0.28 (largest values), 0.37, 0.48, 0.65, 0.85 and 1.20 K. As explained in the text the field is tilted at an angle of 69° from the perpendicular. Dashed lines are fits to eqn.5 plus a quadratic term for $B \cos \theta / T \leq 0.4$ tesla/kelvin.

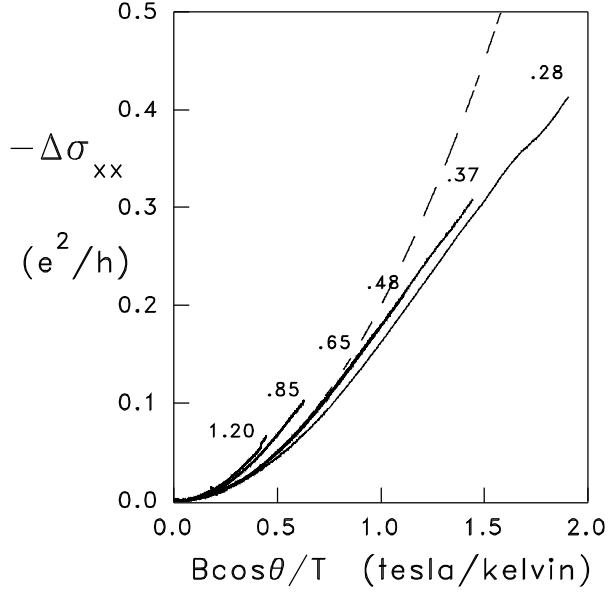


FIG. 5. Residues from data in figure 4 with weak localisation (eqn.5) and classical (eqn.7) terms subtracted off, plotted as a function of $B \cos \theta / T$. Note that data for 0.37, 0.48 and 0.65K overlap and cannot be distinguished. Dashed line is quadratic fit used (with eqn.10) to obtain a value for γ_2 .

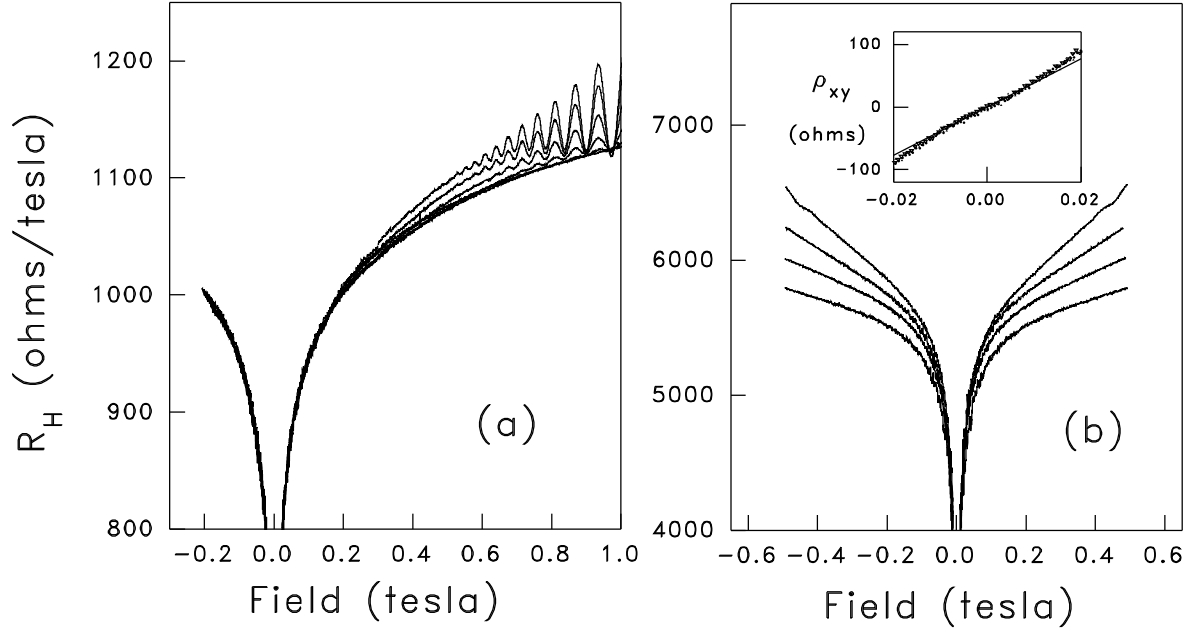


FIG. 6. Hall coefficient as a function of field. (a) Sample A at temperatures of 0.27, 0.39, 0.48, 0.85, 1.20 and 1.89K (R_H decreases with increasing temperature). (b) Sample B at temperatures of 0.28, 0.45, 0.75 and 1.20K. Inset shows the very low field ρ_{xy} data with a straight line corresponding to $R_H = 3850$ ohms/tesla. The periodicity of the Shubnikov-de Haas oscillations corresponds to a Hall coefficient of 1085 ohms/tesla for sample A, and 5000 ohms/tesla for sample B.

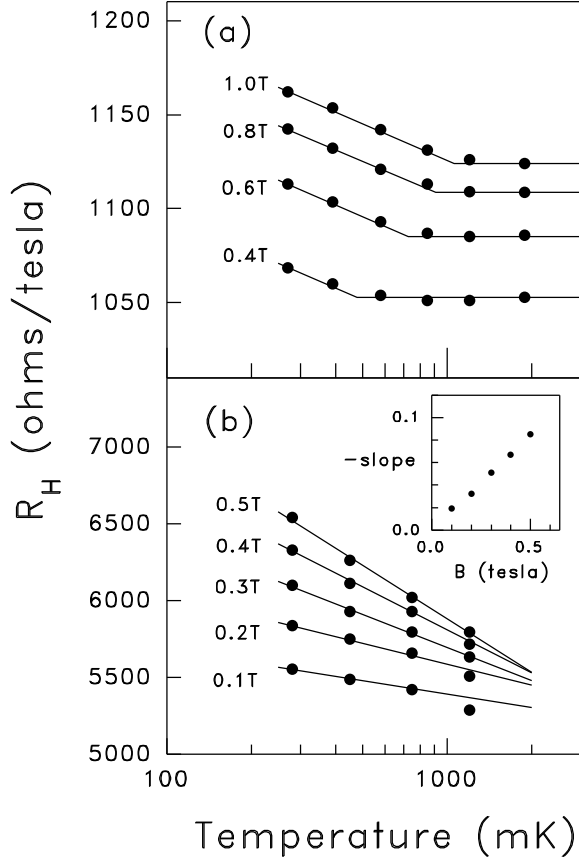


FIG. 7. Hall coefficient as a function of temperature. (a) Sample A at fields of 0.4, 0.6, 0.8 and 1.0 tesla. Lines are a “guide to the eye” showing the transition between temperature independent values at high T and a constant slope at lower T. (b) Sample B at fields of 0.1 - 0.5 tesla. The slopes indicated by the solid lines are plotted in the inset.

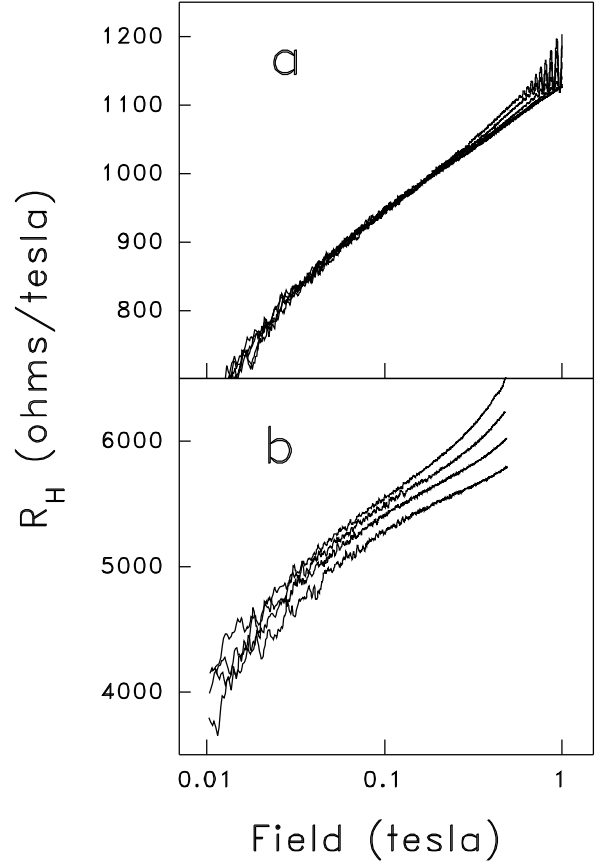


FIG. 8. Semi-logarithmic plot of the Hall coefficient as a function of field. Temperatures as in figure 6. (a) Sample A; (b) Sample B.

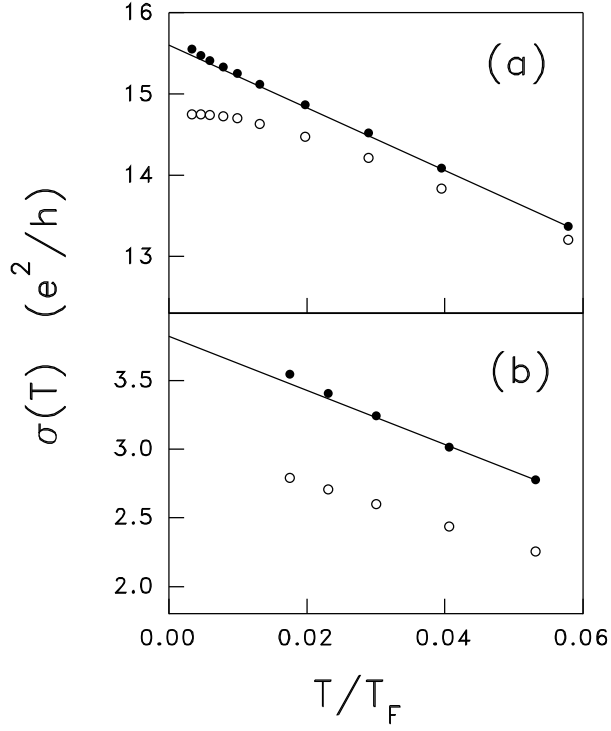


FIG. 9. Zero field conductivity plotted against T/T_F . (a) Sample A with $T_F = 76K$. (b) Sample B with $T_F = 16K$. In each case the open points are the measured data and the solid points have a $\ln(T)$ weak localisation correction subtracted. Solid lines are linear fits to the high T values.